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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			Application Number	10/810,718-Conf. #8917	
			Filing Date	March 29, 2004	
			First Named Inventor	Penayotis C. Andricacos	
			Art Unit	1753	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	20140-0255-US3

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	AA**	US-5,484,518	01/1998	GOLDBERG	
	AB**	US-6,261,433	07/2001	LANDAU	
	AC**	US-6,331,237	12/2001	ANDRICACUS et al.	
	AD**	US-6,113,771	09-05-2000	LANDAU et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	BA**	EP-0952242	11-16-1998	LANDAU, et al.	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 808. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. \*\*CITE NO.: Those patent(s) or publication(s) which are marked with an asterisk (\*) next to the Cite No. are not supplied because they were previously cited by or submitted to the Office in a prior application relied upon in this application for an earlier filing date under 35 U.S.C. 120. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kind Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.			
	CA**	A Novel Electrolyte Composition for Copper Plating in Wafer Metallization; Electrochemical Processing in ULSI Fabrication and Semiconductor/Metal Deposition II: Proceedings of the International Symposium; P.C.: Uziel LANDAU, et al., The Electrochemical Society, Inc. Proceedings Volume 99-9.			
	CB**	A Model of Superfilling in Damascene Electroplating; H. DELIGIANNI, et al.; The 195 <sup>th</sup> Meeting of Electrochemical Society, Inc. Meeting Abstracts, Volume 99-1 (May 2-6, 1999).			
	CC**	Model of Wafer Thickness Uniformity in an Electroplating Tool; The 195 <sup>th</sup> Meeting of Electrochemical Society, Inc. Meeting Abstracts, Volume 99-1 (May 2-6, 1999).			
	CD**	A Model of Superfilling in Damascene Electroplating; H. DELIGIANNI, et al.; Electrochemical Processing in ULSI Fabrication and Semiconductor/Metal Deposition II: Proceedings of the International Symposium; P.C.: Uziel LANDAU, et al., The Electrochemical Society, Inc., Proceedings Volume 99-9.			
	CE**	Uziel LANDAU, A Novel Electrolyte Composition for Copper Plating in Wafer Metallization, Abstract No. 263.			
	CF**	Model of Wafer Thickness Uniformity in an Electroplating Tool; Electrochemical Processing in ULSI Fabrication and Semiconductor/Metal Deposition II: Proceedings of the International Symposium; P.C.H. DELIGIANNI, et al., The Electrochemical Society, Inc., Proceedings Volume 99-9.			
	CG**	Computational Aspects of the Terminal Effect on Wafer-Scale Uniformity; H. DELIGIANNI et al.; The 195 <sup>th</sup> Meeting of Electrochemical Society, Inc. Meeting Abstracts, Volume 99-1 (May 2-6, 1999).			

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. \*\*CITE NO.: Those patent(s) or publication(s) which are marked with an asterisk (\*) next to the Cite No. are not supplied because they were previously cited by or submitted to the Office in a prior application relied upon in this application for an earlier filing date under 35 U.S.C. 120.

Examiner Signature	Date Considered
<i>[Signature]</i>	3/7/06

Patent unavailable. In LOC 174460  
 06 November 3, 2004. (w) 3/4/06